

Title (en)
A semiconductor device and a method for producing the same

Title (de)
Halbleiteranordnung und Verfahren zur Herstellung

Title (fr)
Dispositif semi-conducteur et son procédé de fabrication

Publication
EP 0530051 B1 19981014 (EN)

Application
EP 92307902 A 19920828

Priority
JP 21903191 A 19910829

Abstract (en)
[origin: EP0530051A2] A semiconductor device includes an insulating substrate; and an electrode wiring provided on an area of the insulating substrate. The electrode wiring is formed of a material selected from the group consisting of an alloy of Ta and Nb, Nb, and a metal mainly including Nb. A method for producing a semiconductor device includes the steps of forming a layer including Nb doped with nitrogen on an insulating substrate by a sputtering method in an atmosphere of an inert gas including nitrogen, and then patterning the layer to form an electrode wiring on an area of the insulating substrate; and forming an oxide film at a portion of the electrode wiring by anodization, the portion including at least a surface thereof. <IMAGE>

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IPC 8 full level
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